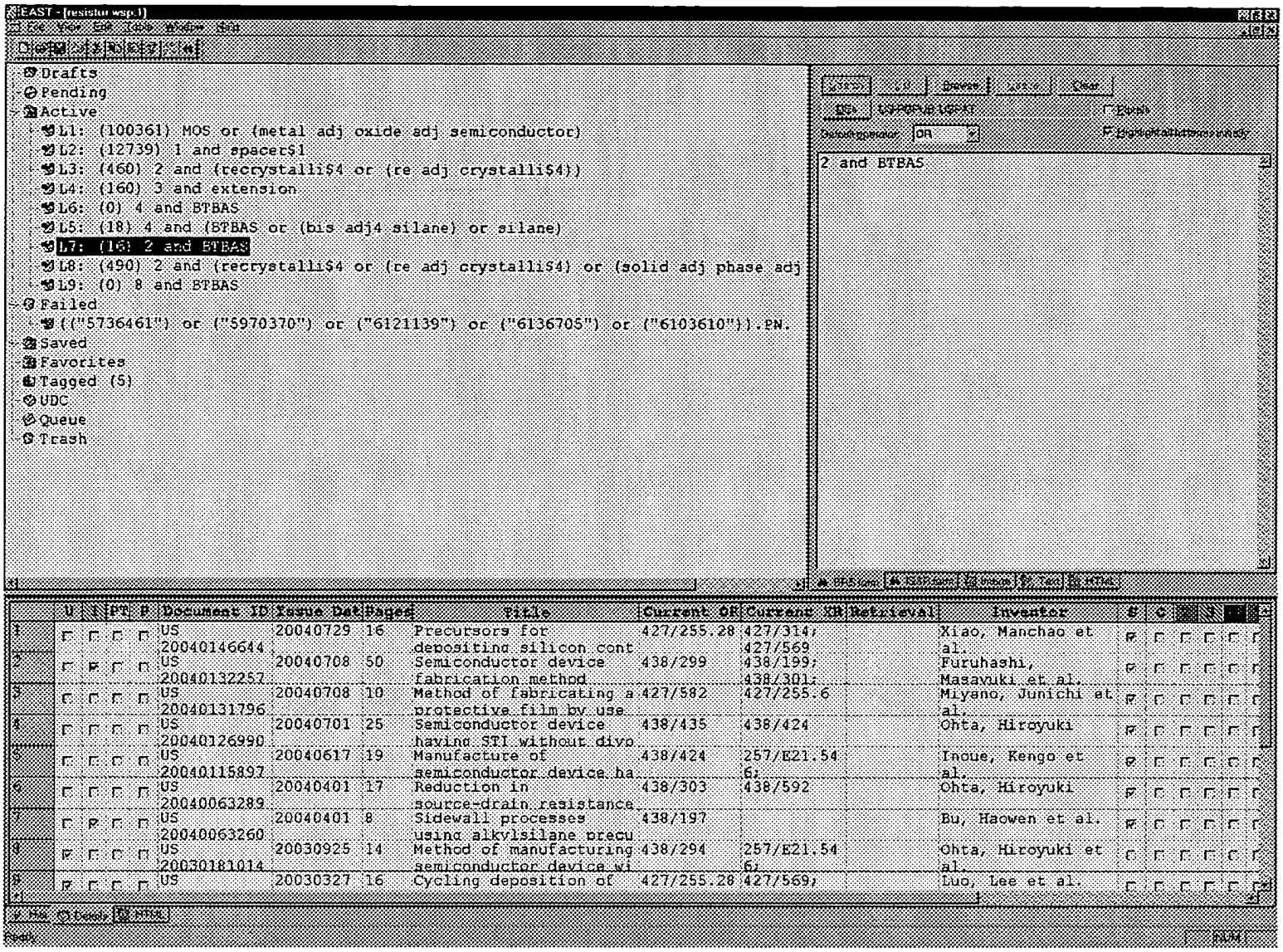
EAST - [resistor.wsp1]
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L1: (100361) MOS or (metal adj oxide adj semiconductor)
L2: (12739) 1 and spacer$1
L3: (460) 2 and (recrystalli$4 or (re adj crystalli$4))
L4: (160) 3 and extension
L6: (0) 4 and BTBAS
L5: (18) 4 and (BTBAS or (bis adj4 silane) or silane)
L7: (16) 2 and BTBAS
L8: (490) 2 and (recrystalli$4 or (re adj crystalli$4) or (solid adj phase adj
L9: (0) 8 and BTBAS
Failed
(("5736461") or ("5970370") or ("6121139") or ("6136705") or ("6103610")).PN.
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2 and BTBAS
U I PT P Document ID Issue Dat Pages Title Current OR Current XR Retrieval Inventor
1 US 20040146644 20040729 16 Precursors for depositing silicon cont 427/255.28 427/314; 427/569 Xiao, Manchao et al.
2 US 20040132257 20040708 50 Semiconductor device fabrication method 438/299 438/199; 438/301; Furuhashi, Masayuki et al.
3 US 20040131796 20040708 10 Method of fabricating a protective film by use 427/582 427/255.6 Miyano, Junichi et al.
4 US 20040126990 20040701 25 Semiconductor device having STI without divo 438/435 438/424 Ohta, Hiroyuki
5 US 20040115897 20040617 19 Manufacture of semiconductor device ha 438/424 257/E21.54 6; Inoue, Kengo et al.
6 US 20040063289 20040401 17 Reduction in source-drain resistance 438/303 438/592 Ohta, Hiroyuki
7 US 20040063260 20040401 8 Sidewall processes using alkylsilane precu 438/197 Bu, Haowen et al.
8 US 20030181014 20030925 14 Method of manufacturing semiconductor device wi 438/294 257/E21.54 6; Ohta, Hiroyuki et al.
9 US 20030327 16 Cycling deposition of 427/255.28 427/569; Luo, Lee et al.
Ready
NUM